优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max T_C = +25°C (Note 9)
40V	3mΩ @ V_{GS} = 10V	100A
	5mΩ @ V_{GS} = 4.5V	100A

Features

- Rated to 175° C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching – Ensures More Reliable and Robust End Application
- Low Rdson – Minimizes Power Losses
- Low Qg – Minimizes Switching Losses

Description

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

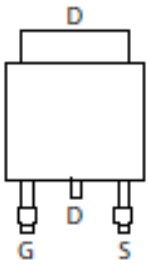
- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

Mechanical Data

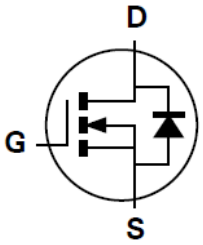
- Case: TO252
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.33 grams (Approximate)

TO252 (DPAK)

Top View



Pin Out Top View



Equivalent Circuit

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	40	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current (Note 6), V_{GS} = 10V	T_C = +25°C (Note 9) T_C = +100°C	I_D	100 100	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I_{DM}	200	A
Maximum Continuous Body Diode Forward Current (Note 6)		I_S	100	A
Avalanche Current, L = 0.2mH		I_{AS}	30	A
Avalanche Energy, L = 0.2mH		E_{AS}	90	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	3.9	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\theta JA}$	38	°C/W
Total Power Dissipation (Note 6)	T_C = +25°C	P_D	180	W
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	0.8	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	40	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current, T_J = +25°C	I_{DSS}	—	—	1	µA	V_{DS} = 32V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	1	—	3	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	2.4	3	mΩ	V_{GS} = 10V, I_D = 50A
		—	4	5	mΩ	V_{GS} = 4.5V, I_D = 50A
Diode Forward Voltage	V_{SD}	—	0.7	1.2	V	V_{GS} = 0V, I_S = 50A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	4,450	—	pF	V_{DS} = 25V, V_{GS} = 0V, f = 1MHz
Output Capacitance	C_{oss}	—	1,407	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	74	—	pF	
Gate Resistance	R_g	—	0.7	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	35	—	nC	V_{DS} = 20V, I_D = 30A
Total Gate Charge (V_{GS} = 10V)	Q_g	—	83	—	nC	
Gate-Source Charge	Q_{gs}	—	10	—	nC	
Gate-Drain Charge	Q_{gd}	—	11.2	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	5.9	—	ns	V_{GS} = 10V, V_{DS} = 20V, R_g = 1.6Ω, I_D = 30A
Turn-On Rise Time	t_r	—	13.2	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	25.8	—	ns	
Turn-Off Fall Time	t_F	—	7.9	—	ns	
Body Diode Reverse Recovery Time	t_{RR}	—	48	—	ns	I_F = 50A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q_{RR}	—	72	—	nC	I_F = 50A, di/dt = 100A/µs

Notes: 5. Device mounted with exposed drain pad on 25mm by 25mm 2oz copper on a single- sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady state.
6. Thermal resistance from junction to solder point (on the exposed drain pin).
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.
9. Package Limited.

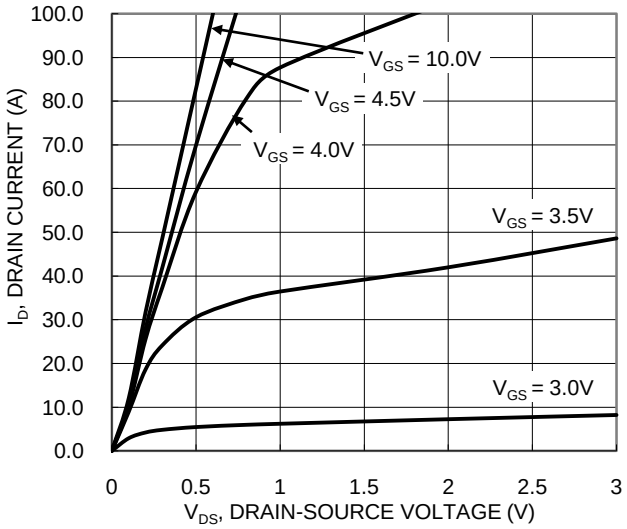


Figure 1. Typical Output Characteristic

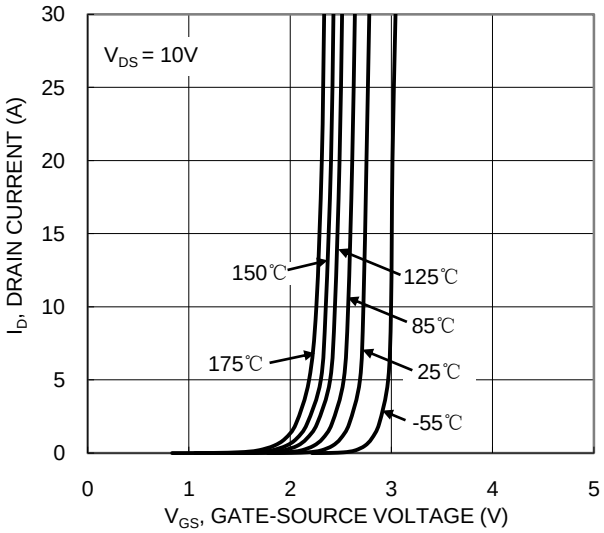


Figure 2. Typical Transfer Characteristic

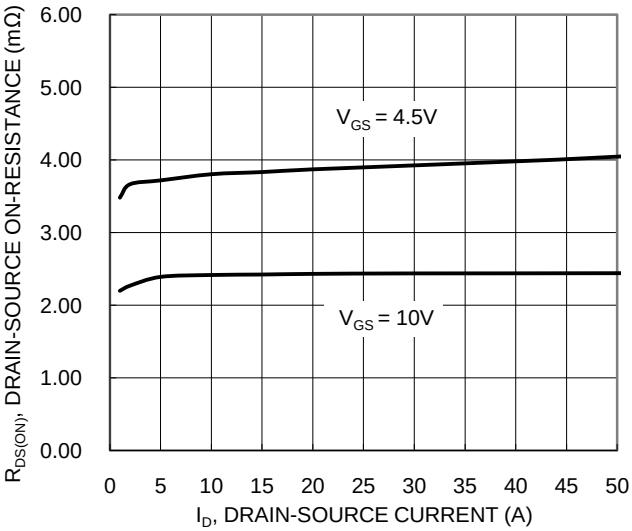


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

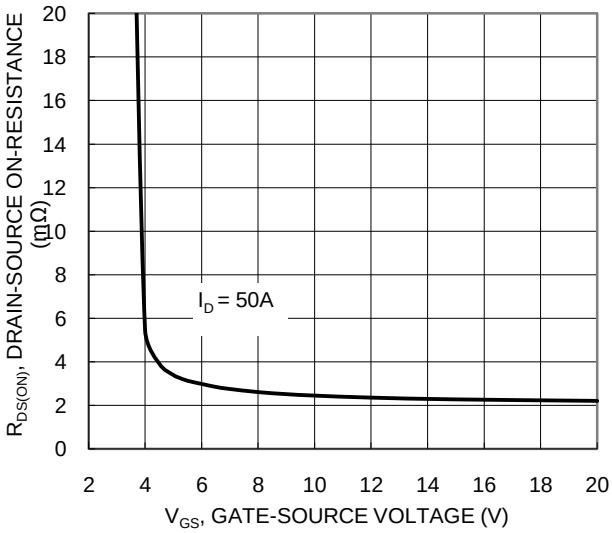


Figure 4. Typical Transfer Characteristic

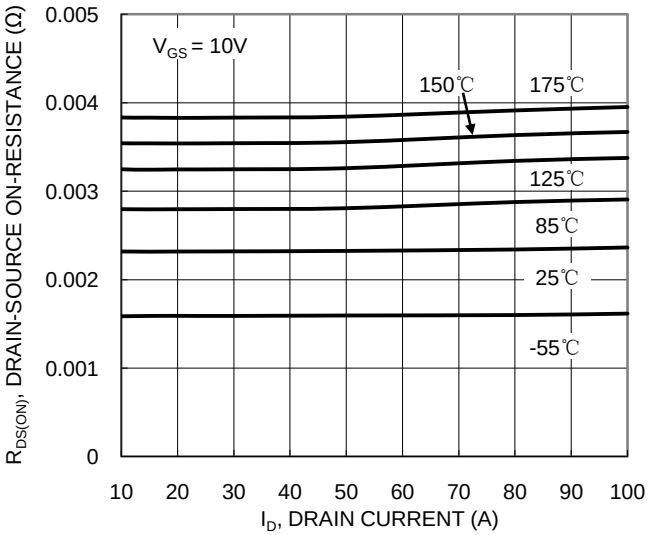


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

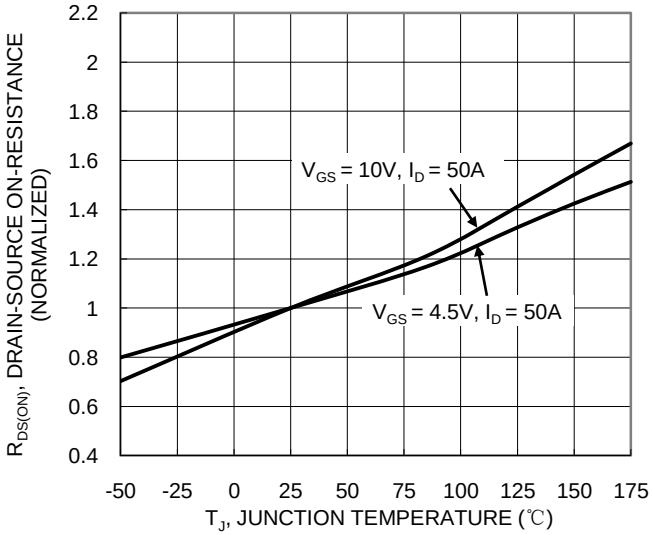


Figure 6. On-Resistance Variation with Temperature

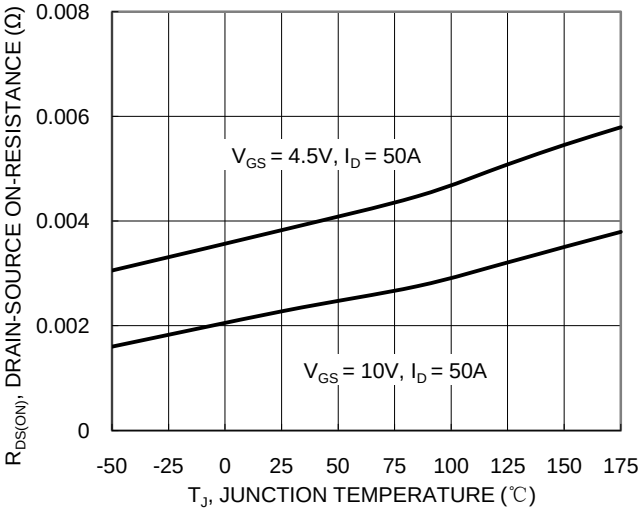


Figure 7. On-Resistance Variation with Temperature

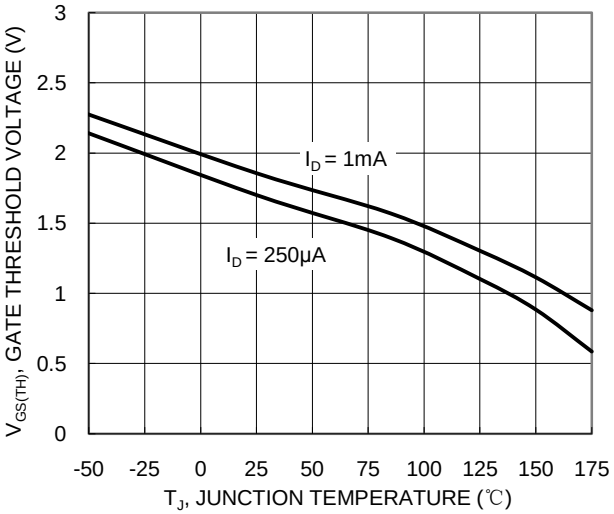


Figure 8. Gate Threshold Variation vs. Temperature

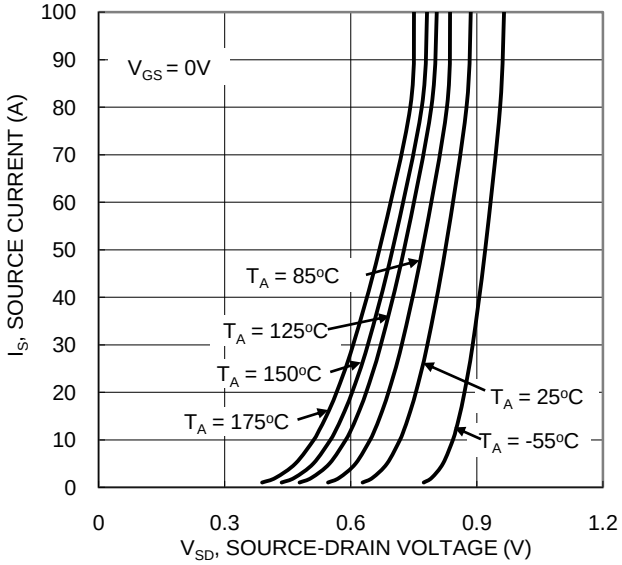


Figure 9. Diode Forward Voltage vs. Current

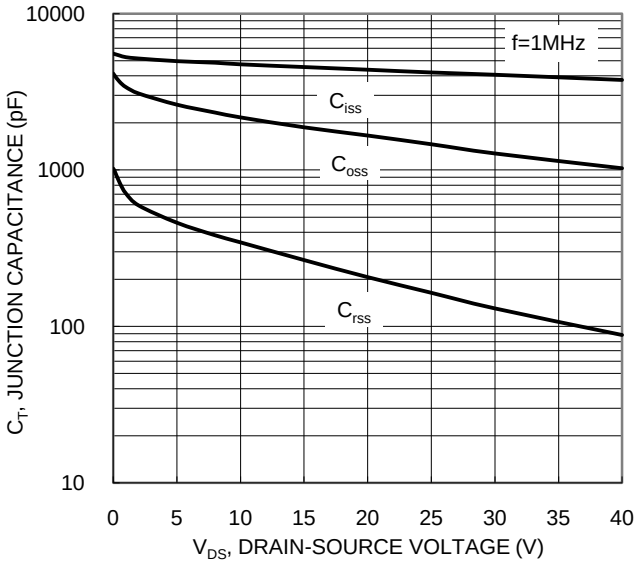


Figure 10. Typical Junction Capacitance

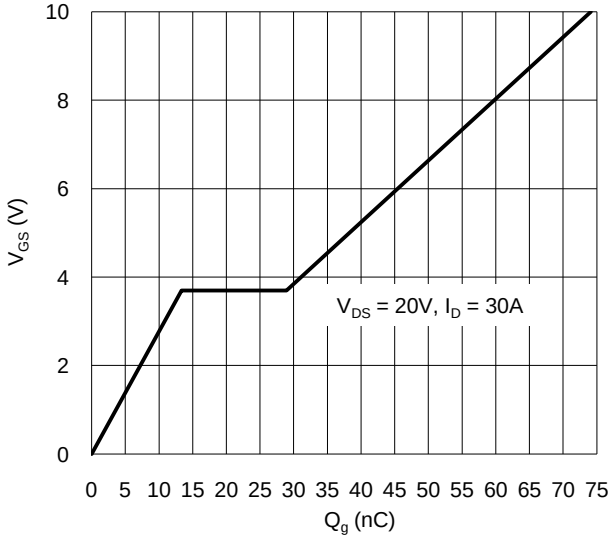


Figure 11. Gate Charge

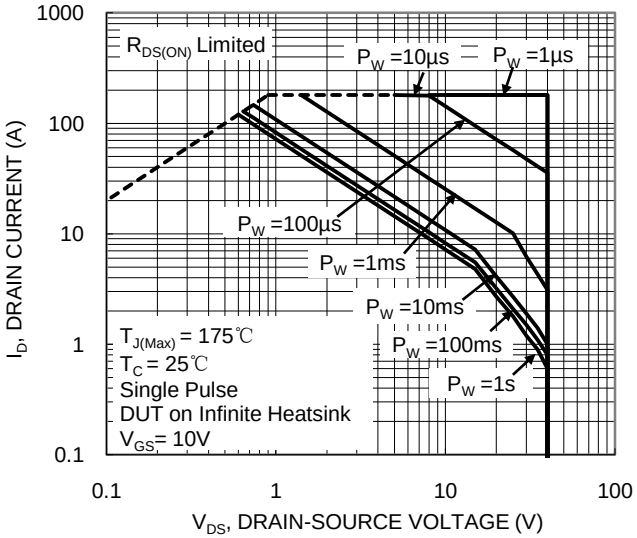


Figure 12. SOA, Safe Operation Area

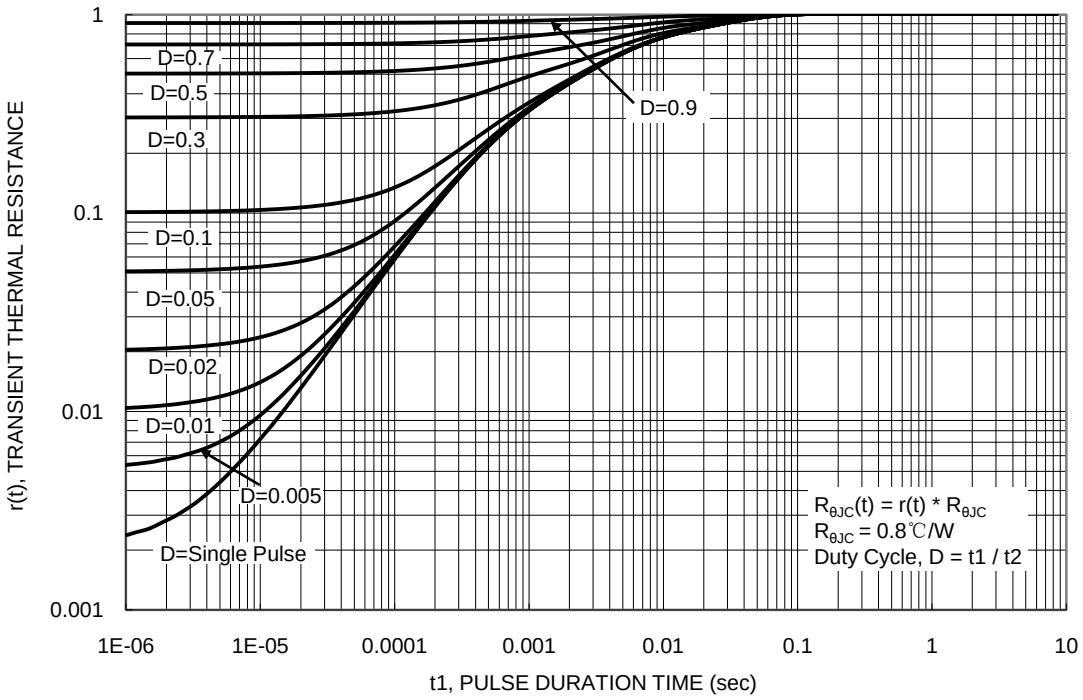
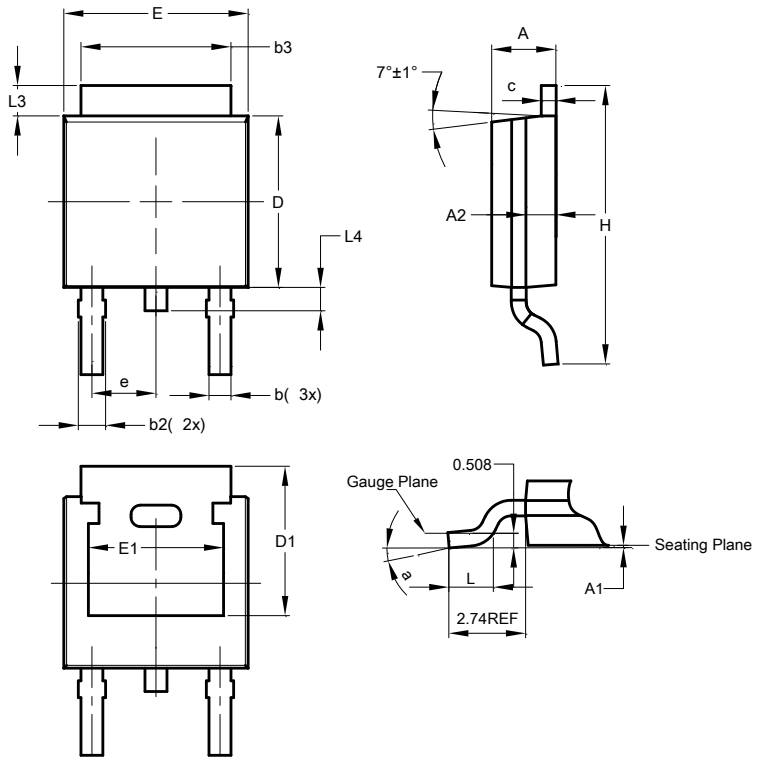


Figure 13. Transient Thermal Resistance

Package Outline

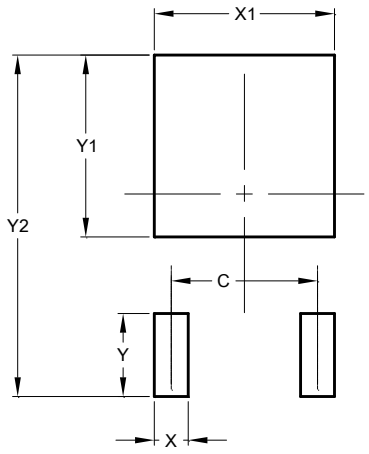
TO252 (DPAK)



TO252 (DPAK)			
Dim	**Min**	**Max**	**Typ**
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	-	-
e	-	-	2.286
E	6.45	6.70	6.58
E1	4.32	-	-
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	-
All Dimensions in mm			

Suggested Pad Layout

TO252 (DPAK)



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700